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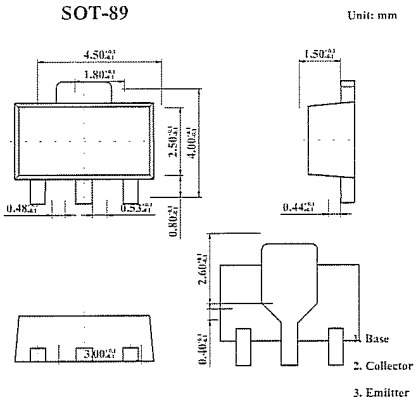
2SC3906

PNP Epitaxial Planar Transistor

- **General Purpose switching**
- **Amplifier applications**



Absolute Maximum Ratings Ta=25℃

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current	-200	mA
P_C	Collector Dissipation	1,000	mW
T_J	Junction Temperature	150	℃
T_{STG}	Storage Temperature	-55~150	℃

Electrical Characteristics Ta=25℃

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C=-100 μ A, I_E=0	-60		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C=-1mA, I_B=0	-40		V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E=-100 μ A, I_C=0	-5		V
I_{CEO}	Collector-emitter Cut-off Current	V_{CE}=-30V, V_{BE}=-3V		50	η A
h_{FE}	DC Current Gain	V_{CE}=-1V, I_C=-100μA V_{CE}=-1V, I_C=-1mA V_{CE}=-1V, I_C=-10mA V_{CE}=-1V, I_C=-50mA V_{CE}=-1V, I_C=-100mA	60 80 100 60 30	300	
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C=-10mA, I_B=-1mA I_C=-50mA, I_B=-5mA		-250 -400	mV
V_{BE}(sat)	Base-Emitter Saturation Voltage	I_C=-10mA, I_B=-1mA I_C=-50mA, I_B=-5mA	-650	-850 -950	mV
f_T	Transition Frequency	V_{CE}=-20V, I_C=-10mA, f=100MHz	250		MHz
C_{ob}	Collector Output Capacitance (Common base, input open circuited)	V_{CB}=-5.0V, f=1MHz		4.5	pF